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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Cohen et al.

Serial No. 09/612,260

Group Art Unit: 2811

Filed: July 7, 2000

Examiner: Kang, Donghee

For: SELF-ALIGNED GATE MOSFET WITH SEPARATE GATES

Assistant Commissioner of Patents  
Box AF  
Washington, D.C. 20231

## AMENDMENT UNDER 37 C.F.R. 1.116

Sir:

In response to the Office Action mailed September 20, 2002, please amend the above-identified patent application as follows:

IN THE CLAIMS:

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Please cancel claims 45, 46 and 49 without prejudice or disclaimer.

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Please add the following new claims.

52. The transistor in claim 1, wherein a material composition of said second gate is independent of a material composition of said isolation layer.
53. The transistor in claim 1, wherein said channel region comprises single crystal silicon.
54. The transistor in claim 44, wherein said channel region includes an extension into said source and drain regions.

**CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)**Applicant(s): **Cohen et al.**

Docket No.

**YOR9-2000-0174**

Serial No.

**09/612,260**

Filing Date

**July 7, 2000**

Examiner

**D. Kang**

Group Art Unit

**2811**Invention: **SELF-ALIGNED GATE MOSFET WITH SEPARATE GATES**

I hereby certify that this

**Amendment Under 37 CFR 1.116***(Identify type of correspondence)*is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. **703-872-9319**)on **November 19, 2002***(Date)***Frederick W. Gibb, III***(Typed or Printed Name of Person Signing Certificate)**(Signature)***FAX RECEIVED**

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